

Product Overview

FDMC510P: P-Channel PowerTrench® MOSFET, -20V, -18A, 8.0mΩ

For complete documentation, see the data sheet.

This P-channel MOSFET is produced using an advanced Power Trench® process that has been optimized for RDS(ON), switching performance and ruggedness.

Features

- Max. RDS(on) = 8.0 mΩ at VGS = -4.5 V, ID = -12 A
- Max. RDS(on) = 9.8 mΩ at VGS = -2.5 V, ID = -10 A
- Max. RDS(on) = 13 mΩ at VGS = -1.8 V, ID = -9.3 A
- Max. RDS(on) = 17 mΩ at VGS = -1.5 V, ID = -8.3 A
- High-Performance Trench Technology for Extremely Low RDS(on)
- High Power and Current Handling Capability in a Widely Used Surface-Mount Package
- 100% UIL Tested
- Termination is Lead-Free and RoHS Compliant
- HBM ESD capability level >2KV Typical

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DSS} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
FDMC510P	0.56	Pb-free Halide free	Active	P-Channel	Single	-20	8	-1	-18	41	9.8	8	-	53	83	5910	WDFN-8
FDMC510P-F106	0.4	Pb-free Halide free	Active	P-Channel		-20	8	-1	-18	41	9.8	8	-	53	83	5910	WDFN-8

For more information please contact your local sales support at www.onsemi.com.

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